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Under the Paperwork Reduction Action of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number. Application Number Unknown Substitute for form 1449A/PTO Filing Date Unknown INFORMATION DISCLOSURE First Named Inventor: WOHLMUTH, Walter A. STATEMENT BY APPLICANT Examiner name: Unknown GROUP: Unknown (use as many sheets as necessary) Sheet of 1 Attorney Docket Number **TRO-00004** U.S. PUBLISHED PATENT APPLICATIONS U.S. Patent Document Name of Patentee or Applicant of Cited Date of Publication Pages, Columns, Lines Examiner Kind Code 2 Initials* No. 1 Cited Document of Cited Document Where Relevant Info. Number MM-DD-YYYY (if known) Appear A01 2002-0171076 A1 Danzilio 11/21/02 U.S. PATENT DOCUMENTS Cited Name of Patentee or Applicant of Date of Publication Pages, Columns, Lines Examiner **U.S. Patent Document** Kind Code 2 Initials* No. Cited Document of Cited Document Where Relevant Info. Number (if known) MM-DD-YYYY Appear A02 6,242,293 **B**1 Danzilio 6/5/01 7/10/01 A03 6,258,639 **B1** Rohdin et al. A04 6,307,221 **B1** Danzilio 10/23/01 A05 6,521,961 **B1** 2/18/03 Costa et al. A06 6,555,850 **B1** Sakamoto et al. 4/29/03 A07 6,593,603 **B1** Kim et al. 7/15/03 OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Toyoda et al., "An application of Pt-GaAs reaction to GaAs ICs," Inst. Phys. Conf. Ser. No. 63, Chapter 11, pp. 521-526 (1981) Schulz et al., "Morphological Development During Platinum/Gallium Arsenide Interfacial Reactions," J. of Elect. Mat., 19, #6, pp. 581-589 (1990) Ko, Dae-Hong and Robert Sinclair, "In-situ dynamic high-resolution transmission electron microscopy: application to Pt/GaAs interfacial reactions," Ultramicroscopy, 54, pp. 166-178 (1994) Saka et al., "Low Standby Leakage Current Power Amplifier Module Made with Junction PHEMT Technology," 25th IEEE GaAs IC Symposium Technical Digest, pp. 301-304 (2003)

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EXAMINER

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